

## BC327-25 BC327-40

# SMALL SIGNAL PNP TRANSISTORS

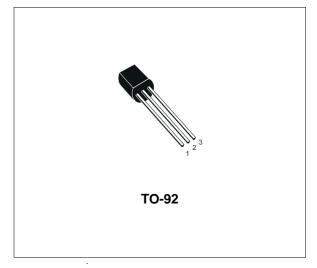
#### PRELIMINARY DATA

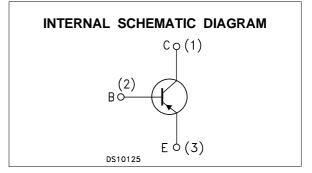
Туре	Marking
BC327-25	BC327-25
BC327-40	BC327-40

- SILICON EPITAXIAL PLANAR PNP TRANSISTORS
- TO-92 PACKAGE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY
- THE NPN COMPLEMENTARY TYPES ARE BC337-25 AND BC337-40 RESPECTIVELY

#### **APPLICATIONS**

- WELL SUITABLE FOR TV AND HOME APPLIANCE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTORS WITH HIGH GAIN AND LOW SATURATION VOLTAGE





#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)	-50	V	
Vceo	Collector-Emitter Voltage (I <sub>B</sub> = 0)	-45	V	
V <sub>EBO</sub>	Emitter-Base Voltage $(I_C = 0)$	-5	V	
Ιc	Collector Current	-0.5	Α	
I <sub>CM</sub>	Collector Peak Current	-1	Α	
P <sub>tot</sub>	Total Dissipation at $T_{C}$ = 25 °C	625	mW	
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

#### THERMAL DATA

R <sub>thj-amb</sub> •	Thermal Resistance Junction-Ambient	Max	200	°C/W
R <sub>thj-case</sub> •	Thermal Resistance Junction-Case	Max	83.3	°C/W

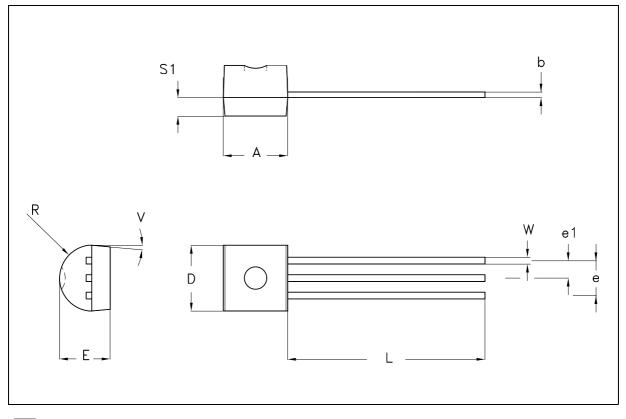
### **ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
І <sub>СВО</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	$V_{CB} = -20 V$ $V_{CB} = -20 V$ $T_{C} = 150 \ ^{\circ}C$			-100 -5	nΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current $(I_C = 0)$	V <sub>EB</sub> = -5 V			-100	nA
V <sub>(BR)</sub> CBO	Collector-Base Breakdown Voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = -10 μA	-50			V
V <sub>(BR)CEO</sub> *	Collector-Emitter Breakdown Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = -10 mA	-45			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = -10 μA	-5			V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	$I_{\rm C} = -500 \text{ mA}$ $I_{\rm B} = -50 \text{ mA}$			-0.7	V
$V_{BE(on)}*$	Base-Emitter On Voltage	I <sub>C</sub> = -500 mA V <sub>CE</sub> = -1 V			-1.2	V
h <sub>FE</sub> *	DC Current Gain	Ic = -100 mA V <sub>CE</sub> = -1 V for <b>BC327-25</b> for <b>BC327-40</b>	160 250		400 600	
f⊤	Transition Frequency	$I_C = -10$ mA $V_{CE} = -5$ V f = 100MHz	80			MHz
Ссво	Collector-Base Capacitance	$I_{E} = 0 \qquad V_{CB} = -10 V  f = 1 MHz$		10		pF

\* Pulsed: Pulse duration = 300  $\mu$ s, duty cycle  $\leq$  2 %

DIM.	mm			inch		
Dini.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.32		4.95	0.170		0.195
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
E	3.30		3.94	0.130		0.155
е	2.41		2.67	0.095		0.105
e1	1.14		1.40	0.045		0.055
L	12.70		15.49	0.500		0.609
R	2.16		2.41	0.085		0.094
S1	1.14		1.52	0.045		0.059
W	0.41		0.56	0.016		0.022
V	4 degree		6 degree	4 degree		6 degree

### TO-92 MECHANICAL DATA



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